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⌘ Title: **TW0405204B: METHOD TO CONTROL THE ETCHING PROCESS**

⌘ Country: **TW Taiwan**

⌘ Kind: **B Patent**

⌘ Inventor: **CHEN, CHIEN-HUNG; Taiwan**  
**WU, JIUN-YUAN; Taiwan**  
**LUR, WATER; Taiwan**


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⌘ Assignee: **UNITED MICROELECTRONICS CORP. Taiwan**  
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⌘ Published /  
Filed: **2000-09-11 / 1998-12-22**

⌘ Application  
Number: **TW1998087121384**

⌘ IPC Code: **H01L 21/76;**

⌘ ECLA Code: **None**

⌘ Priority  
Number: **1998-12-22 TW1998087121384**

⌘ Abstract: The present invention provides a method to control the etching process for striping the dielectric layer on a semiconductor substrate, which comprises the steps as follows: (1) proceed the chemical mechanical polishing on a semiconductor wafer surface to strip a predetermined thickness of the first dielectric layer; (2) measure the residual thickness of said dielectric layer; (3) provide a etching checklist for a plural set of the residual thickness containing all ranges for the dielectric layer and the etching back process or parameters related to the thickness range; and (4) proceed flatly the etching back process according to said checklist to strip the altitude from the first to the second dielectric layer.

⌘ Family:

Buy PDF	Publication	Pub. Date	Filed	Title
<input checked="" type="checkbox"/>	<b>TW0405204B</b>	2000-09-11	1998-12-22	<b>METHOD TO CONTROL THE ETCHING PROCESS</b>
1 family members shown above				

⌘ Other Abstract  
Info:

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